



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Silicon Power Schottky Diode

$V_{RRM} = 20\text{ V} - 100\text{ V}$

$I_F = 200\text{ A}$

Features

- High Surge Capability
- Types up to 100 V V_{RRM}

D-67 Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBRH20020 (R)	MBRH20030 (R)	MBRH20035 (R)	MBRH20040 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		20	30	35	40	V
RMS reverse voltage	V_{RMS}		14	21	25	28	V
DC blocking voltage	V_{DC}		20	30	35	40	V
Continuous forward current	I_F	$T_C \leq 136\text{ °C}$	200	200	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	3000	3000	3000	3000	A
Operating temperature	T_j		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBRH20020 (R)	MBRH20030 (R)	MBRH20035 (R)	MBRH20040 (R)	Unit
Diode forward voltage	V_F	$I_F = 200\text{ A}$, $T_j = 25\text{ °C}$	0.65	0.65	0.65	0.65	V
Reverse current	I_R	$V_R = 20\text{ V}$, $T_j = 25\text{ °C}$	5	5	5	5	mA
		$V_R = 20\text{ V}$, $T_j = 125\text{ °C}$	250	250	250	250	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.8	0.8	0.8	0.8	°C/W
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Figure .1-Typical Forward Characteristics

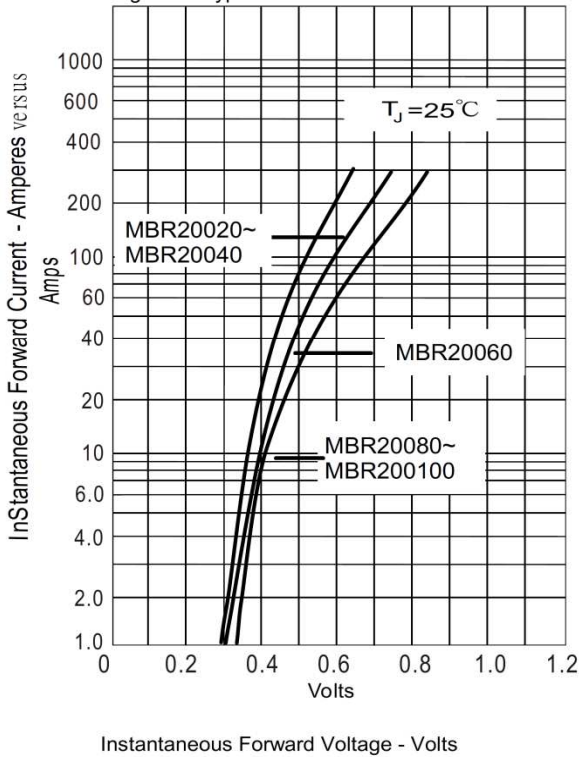


Figure .2- Forward Derating Curve

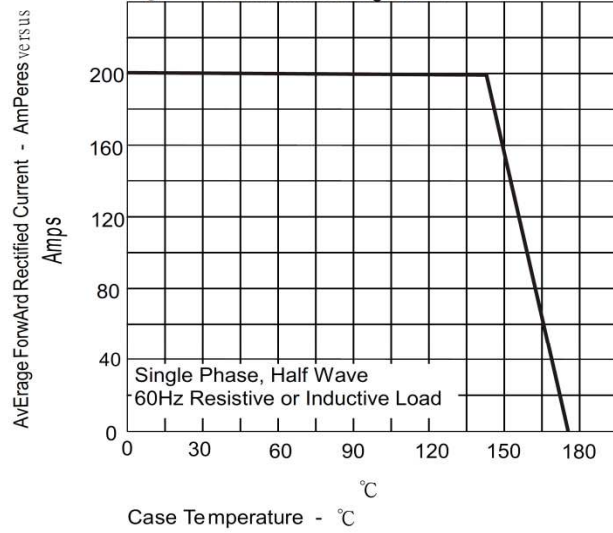


Figure .3-Peak Forward Surge Current

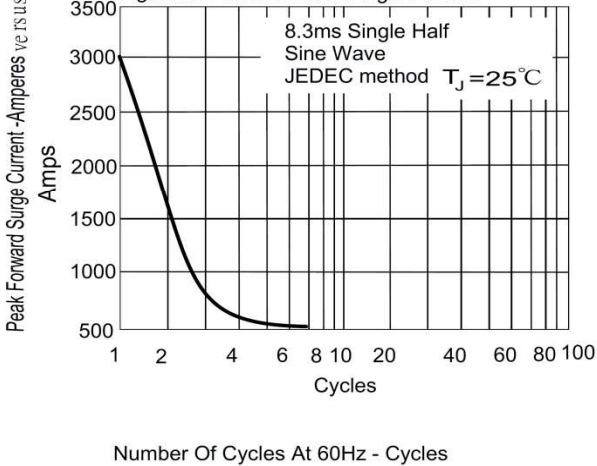


Figure .4-Typical Reverse Characteristics

